



# BUK664R4-55C

N-channel TrenchMOS intermediate level FET

Rev. 03 — 21 December 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Intermediate level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V and 24 V automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a>	[1]	-	-	100 A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	-	204	W
Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <a href="#">Figure 13</a>	-	11.1	13	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <a href="#">Figure 14</a>	-	4.2	4.9	mΩ

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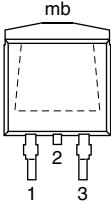
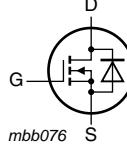
**Table 1.** Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100 \text{ A}$ ; $V_{\text{sup}} \leq 55 \text{ V}$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 \text{ V}$ ; $T_{j(\text{init})} = 25^\circ\text{C}$	-	-	263	mJ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 44 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 18</a> ; see <a href="#">Figure 17</a>	-	31.5	-	nC

[1] Continuous current is limited by package.

## 2. Pinning information

**Table 2.** Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		
SOT404 (D2PAK)				

## 3. Ordering information

**Table 3.** Ordering information

Type number	Package		Version
	Name	Description	
BUK664R4-55C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25^\circ\text{C}; T_j \leq 175^\circ\text{C}$	-	55	V
$V_{GS}$	gate-source voltage	DC	[1]	-16	V
		pulsed	[2]	-20	V
$I_D$	drain current	$T_{mb} = 25^\circ\text{C}; V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	[3]	-	A
		$T_{mb} = 100^\circ\text{C}; V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	-	97	A
$I_{DM}$	peak drain current	$T_{mb} = 25^\circ\text{C}$ ; pulsed; $t_p \leq 10\ \mu\text{s}$ ; see <a href="#">Figure 3</a>	-	550	A
$P_{tot}$	total power dissipation	$T_{mb} = 25^\circ\text{C}$ ; see <a href="#">Figure 2</a>	-	204	W
$T_{stg}$	storage temperature		-55	175	$^\circ\text{C}$
$T_j$	junction temperature		-55	175	$^\circ\text{C}$
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25^\circ\text{C}$	[3]	-	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\ \mu\text{s}; T_{mb} = 25^\circ\text{C}$	-	550	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}; V_{sup} \leq 55\text{ V}; R_{GS} = 50\ \Omega; V_{GS} = 10\text{ V}; T_{j(init)} = 25^\circ\text{C}$	-	263	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[4][5][6]	-	J

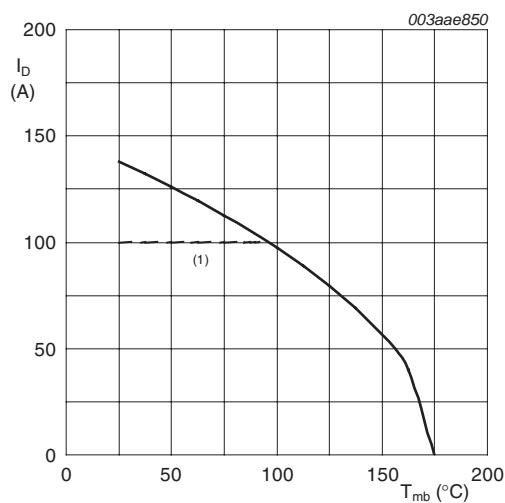
[1] -16 V accumulated duration not to exceed 168 hrs.

[2] Accumulated pulse duration not to exceed 5 mins.

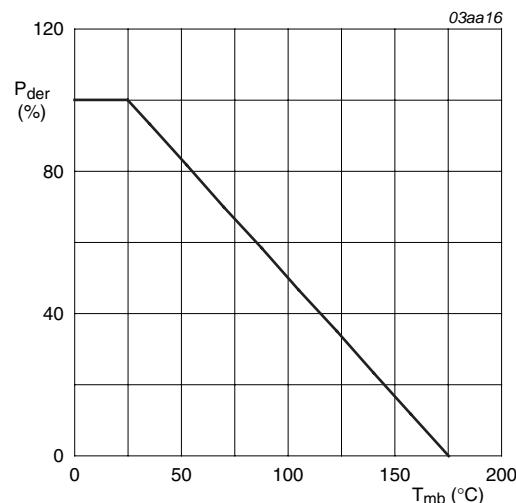
[3] Continuous current is limited by package.

[4] Single-pulse avalanche rating limited by maximum junction temperature of  $175^\circ\text{C}$ .[5] Repetitive avalanche rating limited by an average junction temperature of  $170^\circ\text{C}$ .

[6] Refer to application note AN10273 for further information.

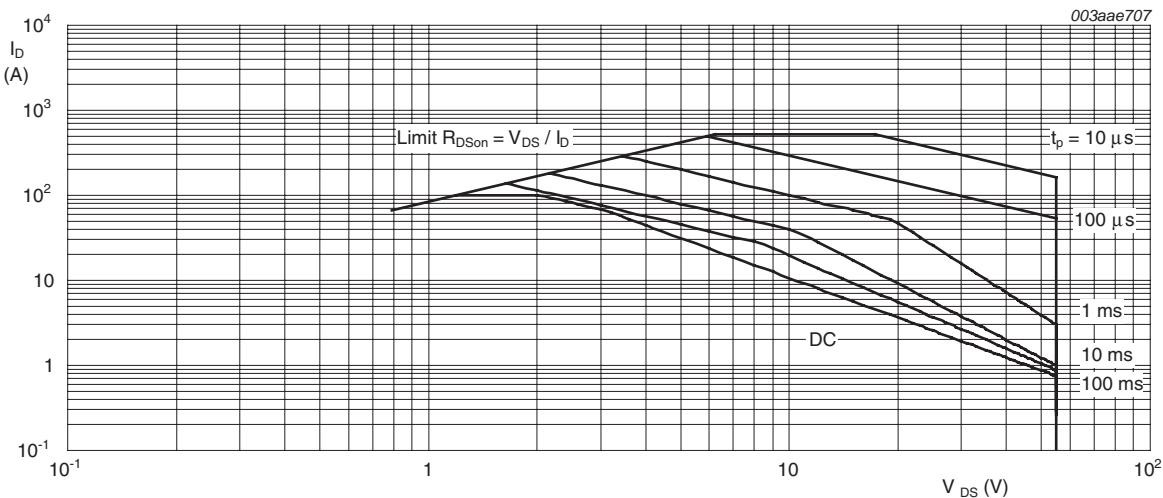


**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot}(25^{\circ}\text{C})} \times 100 \%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



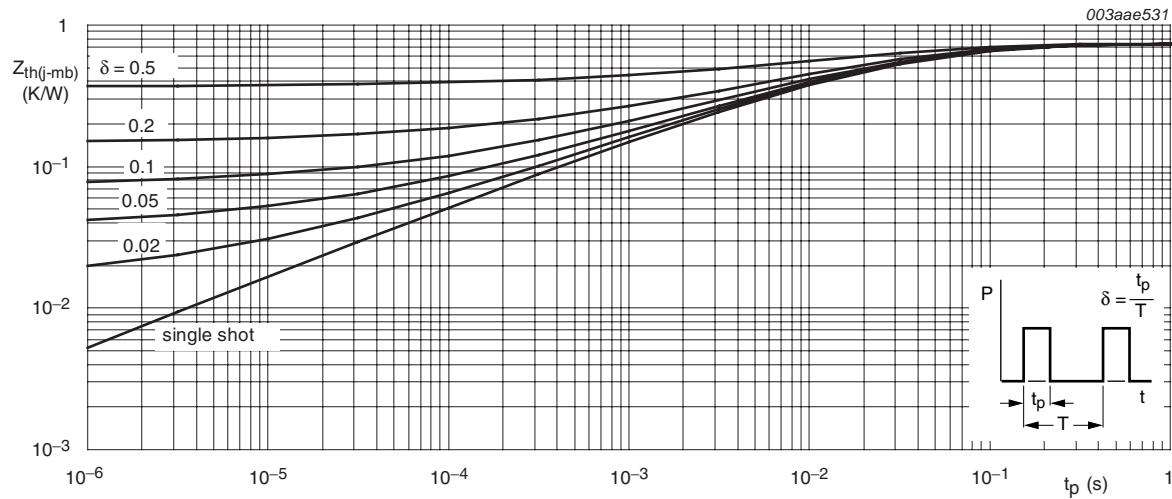
$T_{mb} = 25^{\circ}\text{C}$ ;  $I_{DM}$  is a single pulse

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	0.74	K/W



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

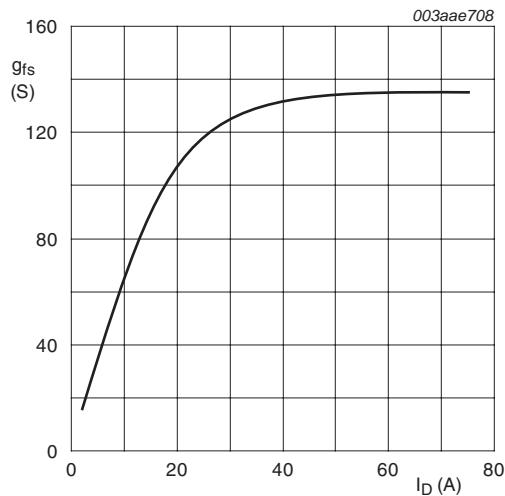
## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25^\circ C$ $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55^\circ C$ $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55^\circ C$	55 27 50	- - -	- - -	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25^\circ C;$ see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a> $I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175^\circ C;$ see <a href="#">Figure 11</a> $I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25^\circ C;$ see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	1.8 0.5 1.1	2.3 - 1.5	2.8 - 2	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55^\circ C;$ see <a href="#">Figure 10</a> $I_D = 2.5 mA; V_{DS} = V_{GS}; T_j = 175^\circ C;$ see <a href="#">Figure 10</a>	- 0.8	- -	3.3 -	V
$I_{DSS}$	drain leakage current	$V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25^\circ C$ $V_{DS} = 30 V; V_{GS} = 0 V; T_j = 175^\circ C$ $V_{DS} = 55 V; V_{GS} = 0 V; T_j = 175^\circ C$	- - -	- - -	1 500 500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25^\circ C$ $V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25^\circ C$ $V_{GS} = -15 V; V_{DS} = 0 V; T_j = 25^\circ C$	- - -	2 2 2	100 100 100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 5 V; I_D = 15 A; T_j = 25^\circ C;$ see <a href="#">Figure 13</a> $V_{GS} = 4.5 V; I_D = 15 A; T_j = 25^\circ C;$ see <a href="#">Figure 13</a> $V_{GS} = 10 V; I_D = 25 A; T_j = 25^\circ C;$ see <a href="#">Figure 14</a> $V_{GS} = 5 V; I_D = 25 A; T_j = 25^\circ C;$ see <a href="#">Figure 14</a> $V_{GS} = 4.5 V; I_D = 25 A; T_j = 25^\circ C;$ see <a href="#">Figure 14</a> $V_{GS} = 10 V; I_D = 15 A; T_j = 25^\circ C;$ see <a href="#">Figure 13</a> $V_{GS} = 10 V; I_D = 25 A; T_j = 175^\circ C;$ see <a href="#">Figure 15</a> ; see <a href="#">Figure 14</a>	- - - - - - - -	11.1 11.4 4.2 5.2 5.7 10 -	13 12 4.9 6.6 7.7 11.7 10.8	$m\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 45 A; V_{DS} = 15 V; V_{GS} = 4.5 V;$ $T_j = 25^\circ C;$ see <a href="#">Figure 16</a> ; see <a href="#">Figure 17</a> $I_D = 25 A; V_{DS} = 44 V; V_{GS} = 5 V;$ see <a href="#">Figure 18</a> ; see <a href="#">Figure 17</a> $I_D = 25 A; V_{DS} = 44 V; V_{GS} = 10 V;$ see <a href="#">Figure 17</a> ; see <a href="#">Figure 18</a>	- - -	5.9 67 124	- - -	C nC nC

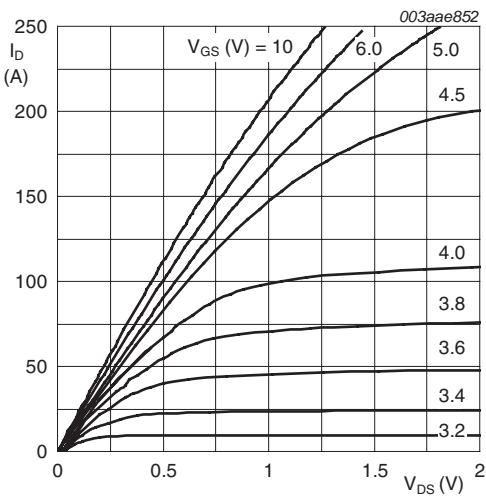
**Table 6. Characteristics ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 18</a> ; see <a href="#">Figure 17</a>	-	19	-	nC
$Q_{GD}$	gate-drain charge		-	31.5	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25^\circ\text{C}$ ; see <a href="#">Figure 19</a>	-	5800	7750	pF
$C_{oss}$	output capacitance		-	550	660	pF
$C_{rss}$	reverse transfer capacitance		-	380	520	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 45 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 10 \Omega$	-	25	-	ns
$t_r$	rise time		-	65	-	ns
$t_{d(off)}$	turn-off delay time		-	252	-	ns
$t_f$	fall time		-	116	-	ns
$L_D$	internal drain inductance	from source lead to source bond pad ; $T_j = 25^\circ\text{C}$	-	7.5	-	nH
$L_S$	internal source inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25^\circ\text{C}$	-	3.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25^\circ\text{C};$ see <a href="#">Figure 20</a>	-	0.83	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}$	-	55	-	ns
$Q_r$	recovered charge		-	112	-	nC



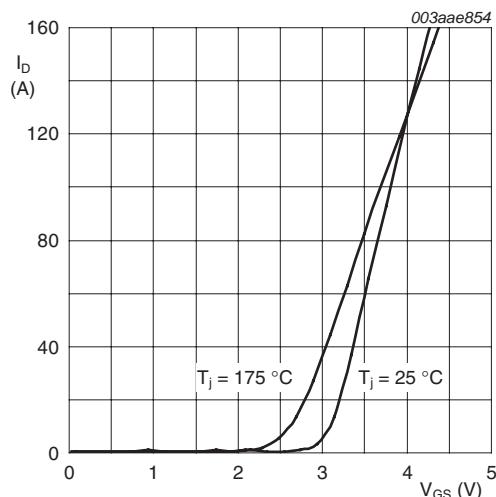
$T_j = 25^\circ\text{C}; V_{DS} = 25 \text{ V}$

**Fig 5. Forward transconductance as a function of drain current; typical values**



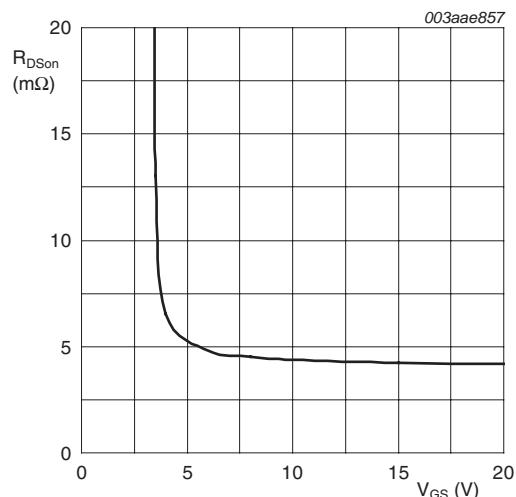
$T_j = 25^\circ\text{C}$

**Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values**

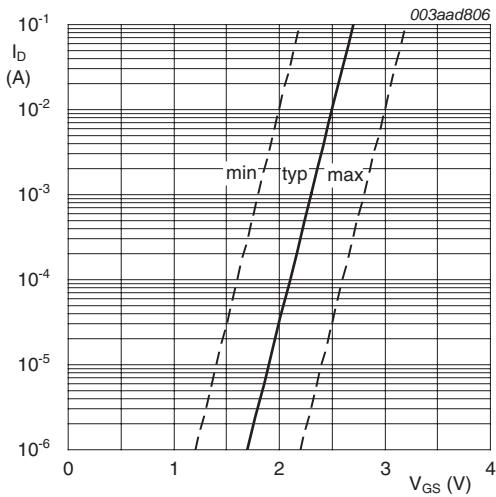


$$V_{DS} > I_D \times R_{DSon}$$

**Fig 7.** Transfer characteristics: drain current as a function of gate-source voltage; typical values

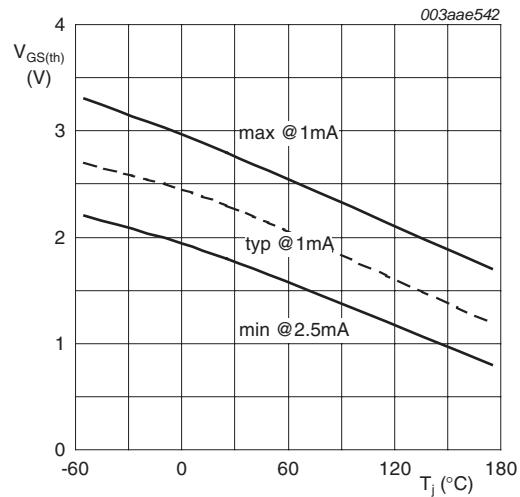


**Fig 8.** Drain-source on-state resistance as a function of gate-source voltage; typical values



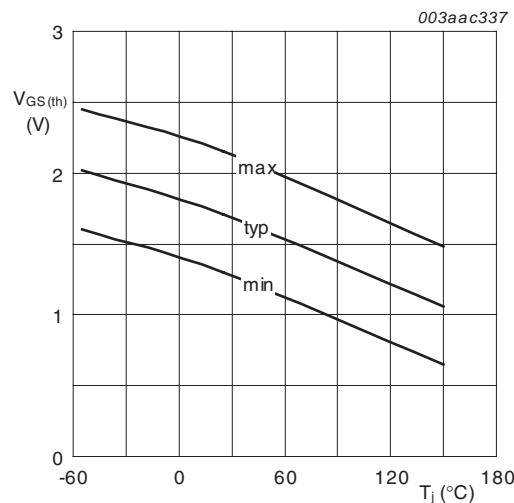
$$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$$

**Fig 9.** Sub-threshold drain current as a function of gate-source voltage

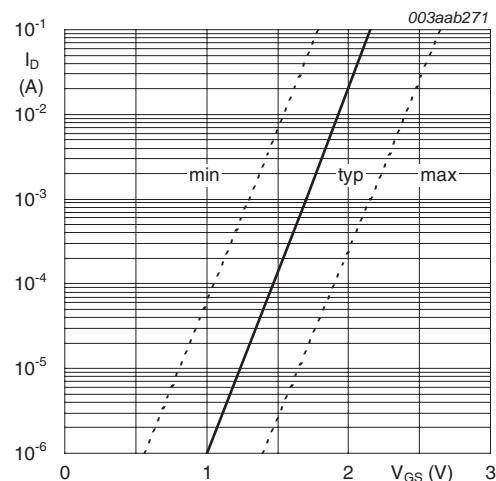


$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

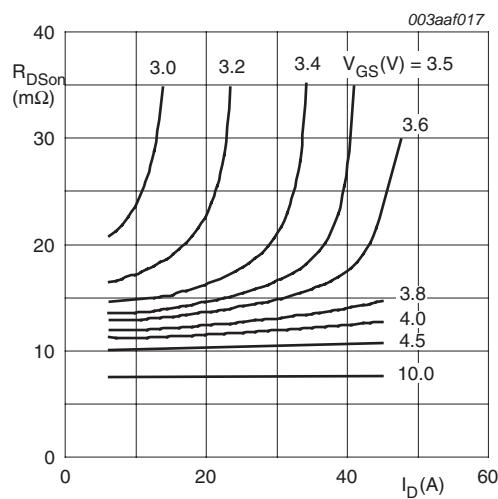
**Fig 10.** Gate-source threshold voltage as a function of junction temperature


 $I_D = 1mA; V_{DS} = V_{GS}$ 

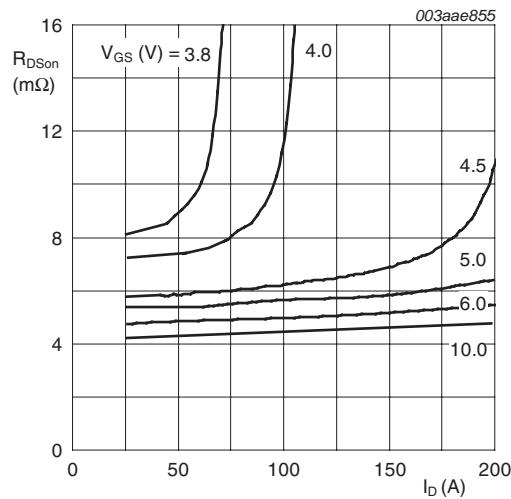
**Fig 11. Gate-source threshold voltage as a function of junction temperature**


 $T_j = 25^{\circ}C; V_{DS} = 5V$ 

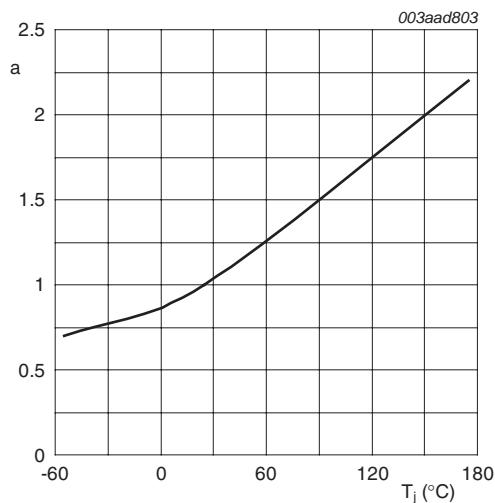
**Fig 12. Sub-threshold drain current as a function of gate-source voltage**


 $T_j = 25^{\circ}C$ 

**Fig 13. Drain-source on-state resistance as a function of drain current; typical values**

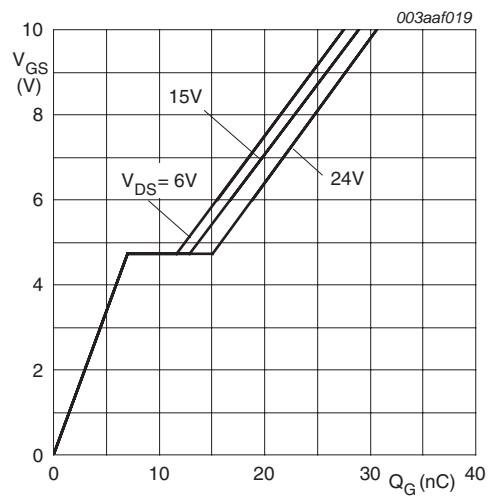

 $T_j = 25^{\circ}C$ 

**Fig 14. Drain-source on-state resistance as a function of drain current; typical values**



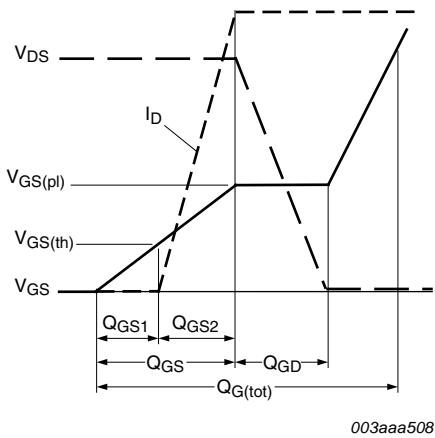
$$a = \frac{R_{DSon}}{R_{DSon}(25\text{ }^{\circ}\text{C})}$$

**Fig 15.** Normalized drain-source on-state resistance factor as a function of junction temperature

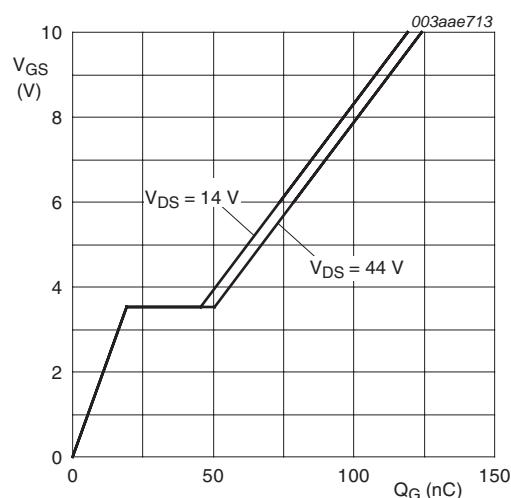


$T_j = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

**Fig 16.** Gate-source voltage as a function of gate charge; typical values

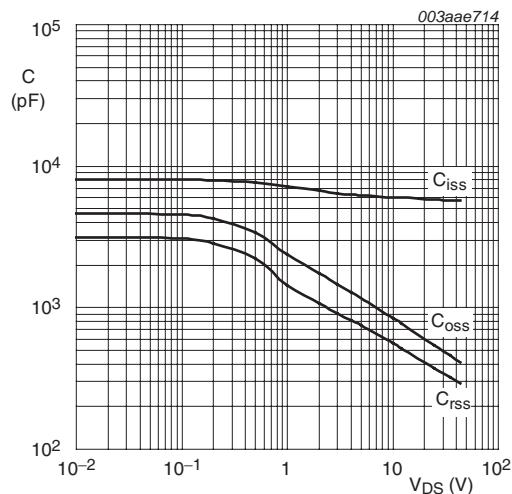


**Fig 17.** Gate charge waveform definitions



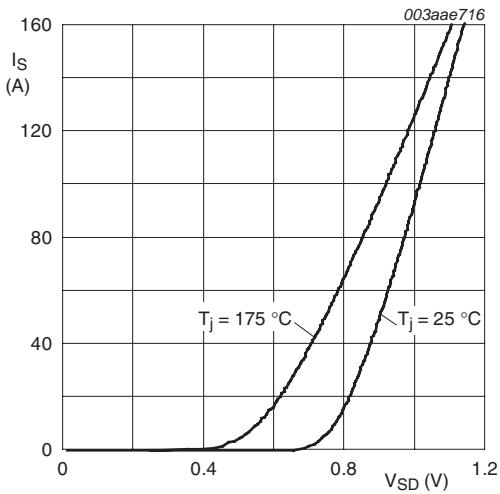
$T_j = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

**Fig 18.** Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

**Fig 19.** Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0 \text{ V}$

**Fig 20.** Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## 7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

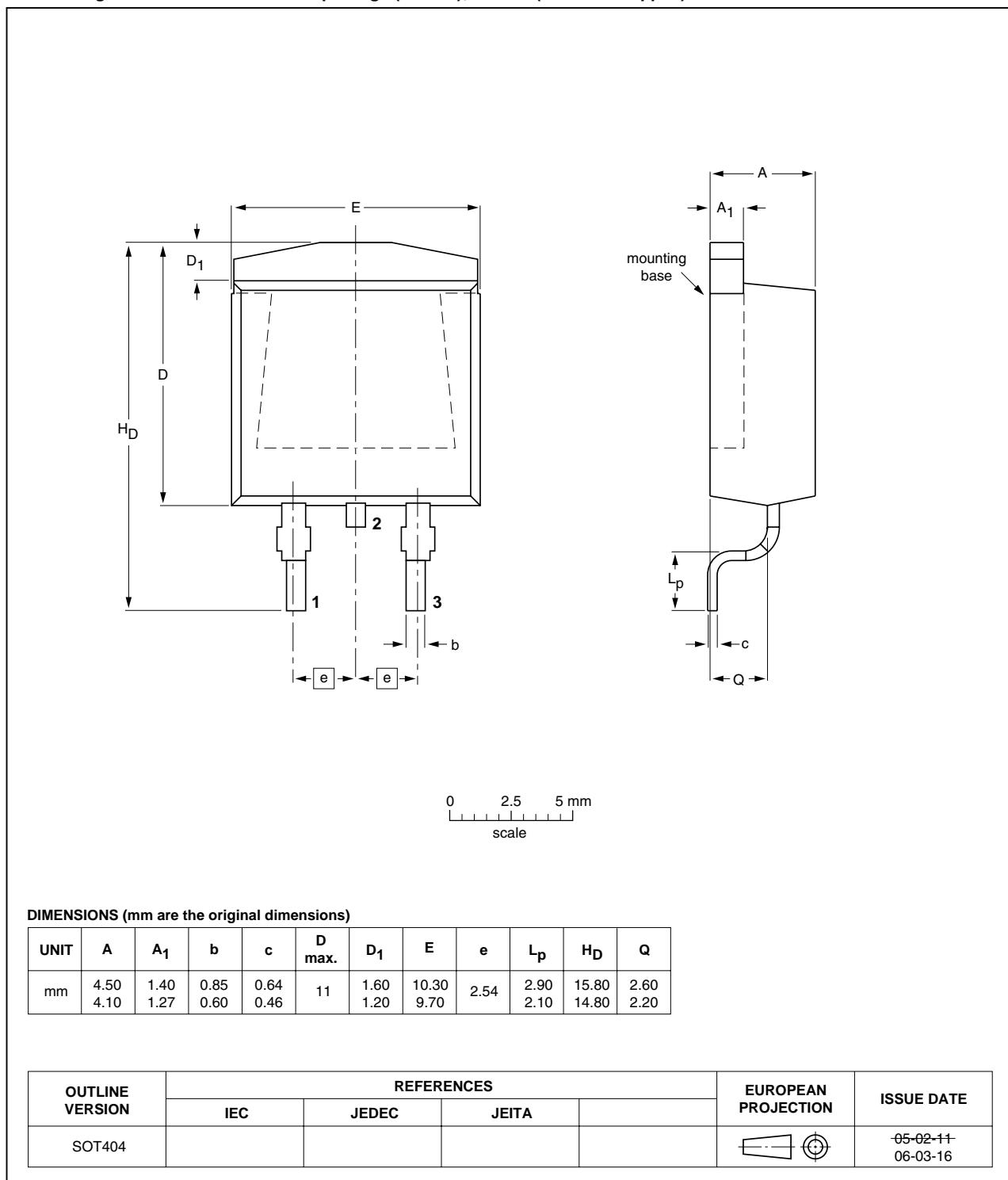


Fig 21. Package outline SOT404 (D2PAK)

## 8. Revision history

**Table 7. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK664R4-55C v.3	20101221	Product data sheet	-	BUK664R4-55C v.2
Modifications:		<ul style="list-style-type: none"><li>• Status changed from objective to product.</li><li>• Various changes to content.</li></ul>		
BUK664R4-55C v.2	20100923	Objective data sheet	-	BUK664R4-55C v.1

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

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## 10. Contact information

For more information, please visit: <http://www.nexperia.com>

For sales office addresses, please send an email to: [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)

### 9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 11. Contents

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<b>1</b>	<b>Product profile</b>	<b>1</b>
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
<b>2</b>	<b>Pinning information</b>	<b>2</b>
<b>3</b>	<b>Ordering information</b>	<b>2</b>
<b>4</b>	<b>Limiting values</b>	<b>3</b>
<b>5</b>	<b>Thermal characteristics</b>	<b>5</b>
<b>6</b>	<b>Characteristics</b>	<b>6</b>
<b>7</b>	<b>Package outline</b>	<b>12</b>
<b>8</b>	<b>Revision history</b>	<b>13</b>
<b>9</b>	<b>Legal information</b>	<b>14</b>
9.1	Data sheet status	14
9.2	Definitions	14
9.3	Disclaimers	14
9.4	Trademarks	15
<b>10</b>	<b>Contact information</b>	<b>15</b>

单击下面可查看定价，库存，交付和生命周期等信息

[>>Nexperia\(安世\)](#)